

SANYO

No.3709

2SA1798

PNP Epitaxial Planar Silicon Transistor

20V/8A Switching Applications

Features

- Adoption of MBIT processes.
- Low saturation voltage.
- Fast switching speed.
- Large current capacity.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

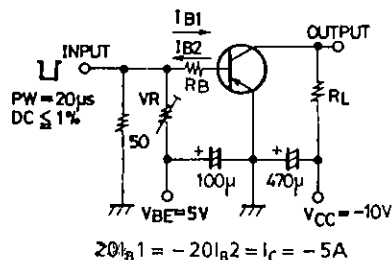
			unit
Collector-to-Base Voltage	V_{CB0}	-25	V
Collector-to-Emitter Voltage	V_{CEO}	-20	V
Emitter-to-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-8	A
Collector Current (Pulse)	I_{CP}	-12	A
Base Current	I_B	-1.5	A
Collector Dissipation	P_C	1.5	W
		10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

 $T_c = 25^\circ\text{C}$ **Electrical Characteristics at $T_a = 25^\circ\text{C}$**

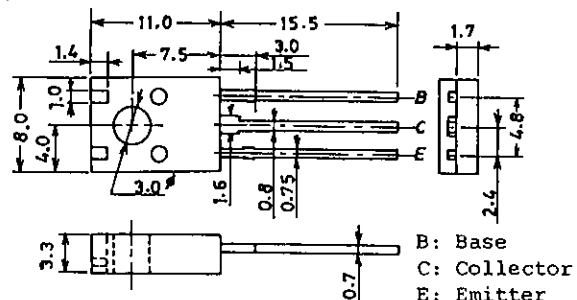
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$			-1	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$	100*		400*	
	$h_{FE}(2)$	$V_{CE} = -2\text{V}, I_C = -6\text{A}$	60			
Gain-Bandwidth Product	f_T	$V_{CE} = -2\text{V}, I_C = -500\text{mA}$		200		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -5\text{A}, I_B = -250\text{mA}$	-220	-400		mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -5\text{A}, I_B = -250\text{mA}$	-1	-1.3		V
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		85		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, R_{BE} = \infty$	-20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
Turn-ON Time	t_{on}	See specified Test Circuit.		30		ns
Storage Time	t_{stg}	"		200		ns
Fall Time	t_f	"		15		ns

* : The 2SA1798 is classified by 500mA h_{FE} as follows.

100 R	200	140 S	280	200 T	400
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Switching Time Test CircuitUnit (Resistance : Ω , Capacitance : F)**Package Dimensions 2042A**

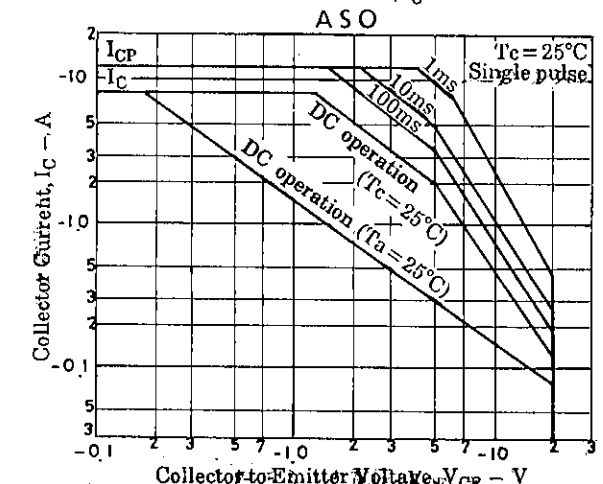
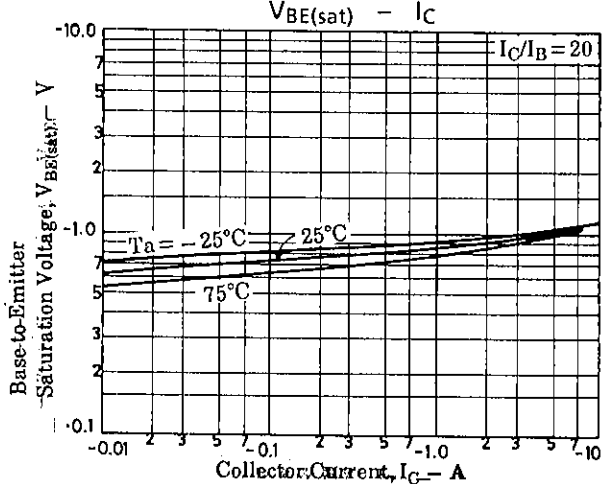
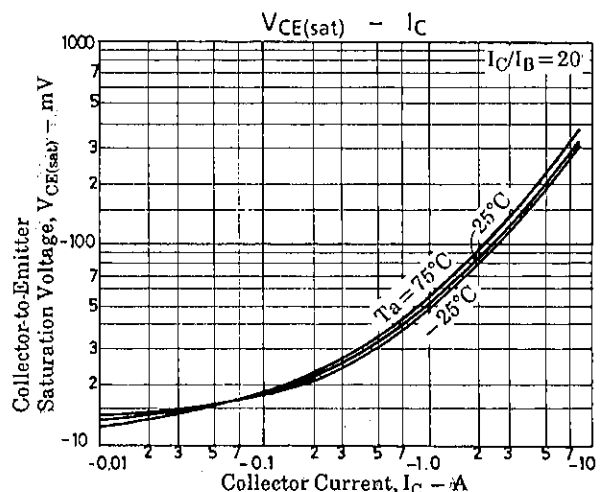
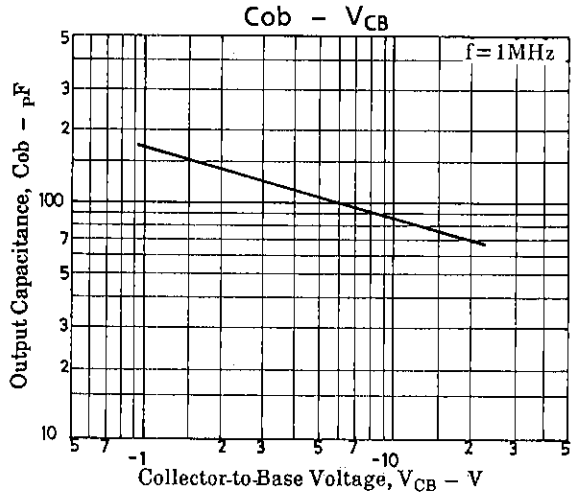
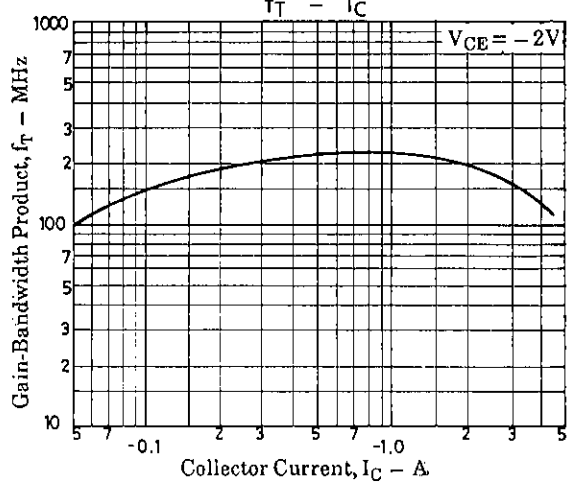
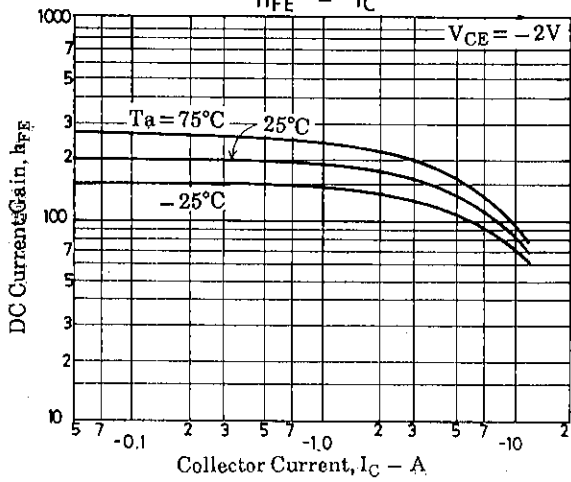
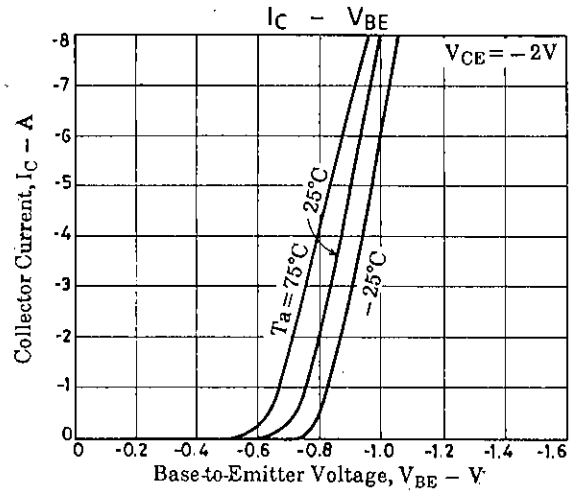
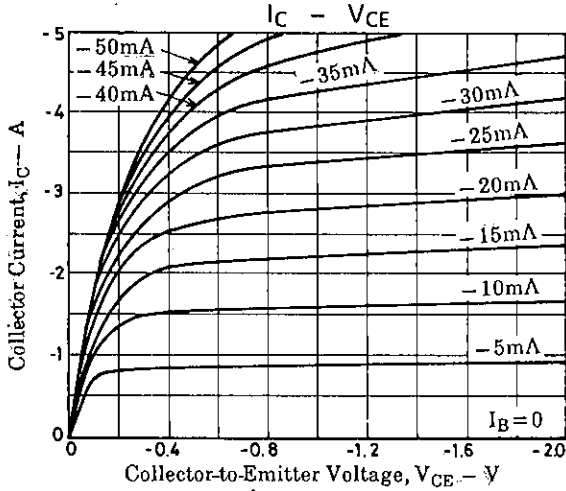
(unit : mm)

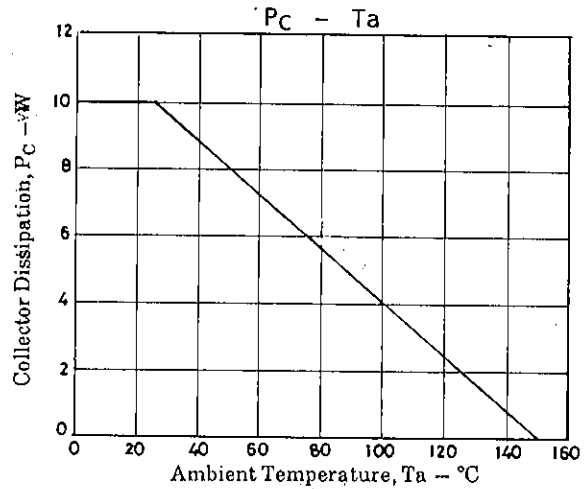
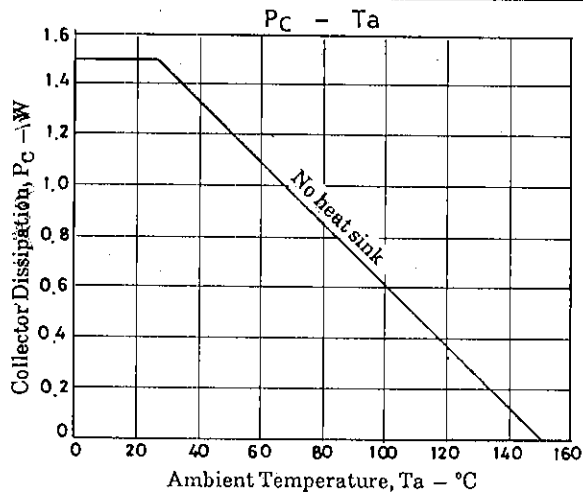


SANYO: TO126ML

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
 TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

5201MH, KOTO No.3709-1/3





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